

**In the specification:**

*Please amend page 2, lines 1-7 as follows:*

U.S. Patent Application No. \_\_\_\_\_ Patent Application No. 09/833,078 to *Thompson et al.*, filed April 12, 2001, entitled "A method for locally modifying the effective bandgap energy in indium gallium arsenide phosphide (InGaAsP) quantum well structures," whose entire disclosure is hereby incorporated by reference into the present disclosure, teaches a method for locally modifying the effective bandgap energy of indium gallium arsenide phosphide (InGaAsP) quantum well structures. That method allows the integration of multiple optoelectronic devices within a single structure, each comprising a quantum well structure. A division of the just-cited patent application has been granted as U.S. Patent No. 6,611,007.